

N-channel TrenchMOS intermediate level FET Rev. 2.1 — 18 August 2011

Product data sheet

1. **Product profile**

1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources

1.3 Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control

1.4 Quick reference data

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	30	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; [1] see <u>Figure 1</u>	-	-	120	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>	-	-	263	W
Static cha	aracteristics					
R_{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u>	-	1.6	1.9	mΩ

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Table 1.	Quick reference data continued					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 120 \text{ A}; \text{V}_{\text{sup}} \leq 30 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; \text{V}_{\text{GS}} = 10 \text{V}; \\ T_{\text{j(init)}} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $	-	-	0.87	J
Dynamic	characteristics					
Q _{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V};$ $V_{GS} = 10 \text{ V};$ see Figure 13; see Figure 14	-	45	-	nC

SOT404 (D2PAK)

[1] Continuous current is limited by package.

Pinning information 2.

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

Ordering information 3.

Table 3. Ordering	j information		
Type number	Package		
	Name	Description	Version
BUK661R8-30C	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	30	V
V _{GS}	gate-source voltage	DC	<u>[1]</u>	-16	16	V
		Pulsed	[2]	-20	20	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[3]	-	120	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[3]	-	120	А
I _{DM}	peak drain current	T _{mb} = 25 °C; pulsed; t _p ≤ 10 μs; see <u>Figure 3</u>		-	1080	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	263	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-dra	in diode					
I _S	source current	T _{mb} = 25 °C	[3]	-	120	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	1080	А
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$ I_D = 120 \text{ A}; \text{V}_{\text{sup}} \leq 30 \text{ V}; \text{R}_{\text{GS}} = 50 \Omega; \\ \text{V}_{\text{GS}} = 10 \text{ V}; \text{T}_{\text{j(init)}} = 25 ^{\circ}\text{C}; \text{ unclamped} $		-	0.87	J
E _{DS(AL)R}	repetitive drain-source avalanche energy		<u>[4][5][6]</u>	-	-	J

[1] -16V accumulated duration not to exceed 168 hrs.

[2] Accumulated pulse duration not to exceed 5mins.

[3] Continuous current is limited by package.

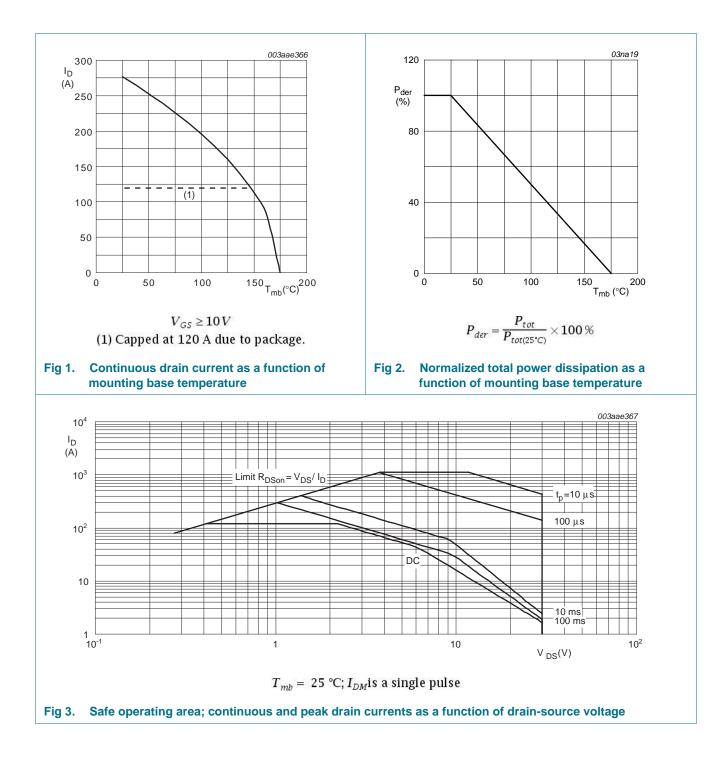
[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[6] Refer to application note AN10273 for further information.

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5. Thermal characteristics

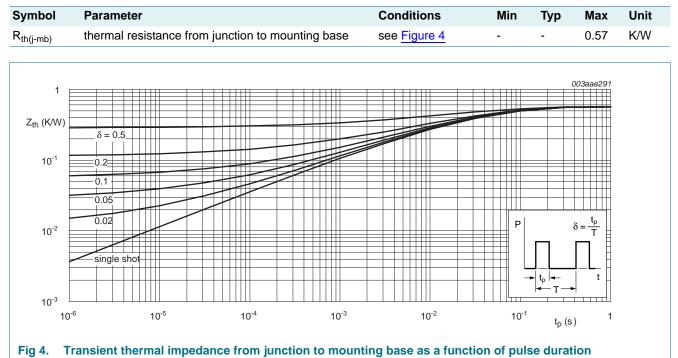


Table 5. Thermal characteristics

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6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics					
V _{(BR)DSS}	drain-source breakdown	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	30	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 10</u>	-	-	3.3	V
		$I_D = 2.5 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see Figure 10	0.8	-	-	V
I _{DSS}	drain leakage current	$V_{DS}=30~V;~V_{GS}=0~V;~T_{j}=25~^{\circ}C$	-	0.02	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	2	100	nA
R _{DSon} drain-source on-s resistance	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u>	-	1.6	1.9	mΩ
		V_{GS} = 4.5 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 11</u>	-	2.48	3.3	mΩ
		V _{GS} = 5 V; I _D = 25 A; T _j = 25 °C; see <u>Figure 11</u>	-	2.24	2.8	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 11</u> ; see <u>Figure 12</u>	-	-	3.6	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 5 \text{ V};$ see Figure 13; see Figure 14	-	95	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$	-	168	-	nC
Q_{GS}	gate-source charge	see Figure 14; see Figure 13	-	27	-	nC
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	45	-	nC
C _{iss}	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	8188	10918	pF
C _{oss}	output capacitance	$T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure } 15}{15}$	-	1327	1592	pF
C _{rss}	reverse transfer capacitance		-	761	1042	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 1 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	43	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$	-	93	-	ns
t _{d(off)}	turn-off delay time		-	272	-	ns
t _f	fall time		-	142	-	ns
L _D	internal drain inductance	from upper edge of drain mounting base to centre of die ; $T_j = 25 \text{ °C}$	-	3.5	-	nH
L _S	internal source inductance	from source lead to source bond pad ; T_j = 25 $^{\circ}\text{C}$	-	7.5	-	nH

Table 6.

Symbol

Characteristics ... continued

Parameter

BUK661R8-30C

Max

Unit

Тур

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Min

Sourco_dr							
	ain diode	$I_{2} = 25 \text{ Av} V$	- 0 \/· T - 25 °C·		0.0	1 0	V
/ _{SD}	source-drain voltage	see Figure 16		-	0.8	1.2	v
r	reverse recovery time		dt = -100 A/µs;	-	62.7	-	ns
۵ _r	recovered charge	$V_{GS} = 0 V; V_D$	_S = 25 V	-	115	-	nC
		003aae293				003aae294	
60	10 5 4.5		80				
I _D			I _D (A)				
(A)			60				
40			00				
10							
			40				
20		3.6		T _j = 175 °C	/ Тј=	= 25 °C	
			20				
		3.4		/			
	V _c	_{iS} (V) = 3.3			$ \mathcal{I} $		
0		V _{DS} (V) ¹	0 1	2	3 4	V _{GS} (V) ⁵	
		VDS(V)				V _{GS} (V)	
	$T_j = 25 ^{\circ}C$			$V_{DS} > I_D \times I_D$	R _{DSon}		
	$T_j = 25 ^{\circ}C$			$V_{DS} > I_D \times I_D$			
	Output characteristics: drain o		Fig 6. Transfer ch	aracteristic	s: drain o		
				aracteristic	s: drain o		
f	Output characteristics: drain o		Fig 6. Transfer ch function of	aracteristic	s: drain o voltage		
f 200	Output characteristics: drain o	ge; typical values	Fig 6. Transfer ch function of	aracteristic	s: drain o voltage	; typical	
f	Output characteristics: drain o	ge; typical values	Fig 6. Transfer ch function of	aracteristic	s: drain o voltage	; typical	
f 200 g _{fs}	Output characteristics: drain o	ge; typical values	Fig 6. Transfer ch function of	aracteristic	s: drain o voltage	; typical	
f 200 g _{fs} (S)	Output characteristics: drain o	ge; typical values	Fig 6. Transfer ch function of	aracteristic	s: drain o voltage	; typical	
f 200 g _{fs} (S)	Output characteristics: drain o	ge; typical values	Fig 6. Transfer ch function of	aracteristic	s: drain o voltage	; typical	
f 200 g _{fs} (S)	Output characteristics: drain o	ge; typical values	Fig 6. Transfer ch function of 15 Γ R _{DSon} (mΩ) Γ 12 Γ	aracteristic	s: drain o voltage	; typical	
f 200 g _{fs} (S) 150	Output characteristics: drain o	ge; typical values	Fig 6. Transfer ch function of 15 Γ R _{DSon} (mΩ) Γ 12 Γ	aracteristic	s: drain o voltage	; typical	
f 200 9 _{fs} (S) 150 100	Output characteristics: drain o	ge; typical values	Fig 6. Transfer ch function of 15	aracteristic	s: drain o voltage	; typical	
f 200 g _{fs} (S) 150	Output characteristics: drain o	ge; typical values	Fig 6. Transfer ch function of 15	aracteristic	s: drain o voltage	; typical	
f 200 9 _{fs} (S) 150 100	Output characteristics: drain o	ge; typical values	Fig 6. Transfer ch function of 15	aracteristic	s: drain o voltage	; typical	
f 200 9 _{fs} (S) 150 100	Dutput characteristics: drain of unction of drain-source voltage	003aae295	Fig 6. Transfer ch function of 15	aracteristic	s: drain (voltage	; typical	
f 200 9 _{fs} (S) 150 100 50	Output characteristics: drain o	ge; typical values	Fig 6. Transfer ch function of	aracteristic	s: drain (voltage	; typical	
f 200 9 _{fs} (S) 150 100 50	Dutput characteristics: drain of unction of drain-source voltage	003aae295	Fig 6. Transfer ch function of	aracteristic: gate-source	s: drain (voltage	; typical	
f 200 ^g fs (S) 150 100 50 0 Fig 7. F	Dutput characteristics: drain of drain-source voltage	003aae295	Fig 6. Transfer ch function of	aracteristic: gate-source	s: drain (voltage	; typical	value

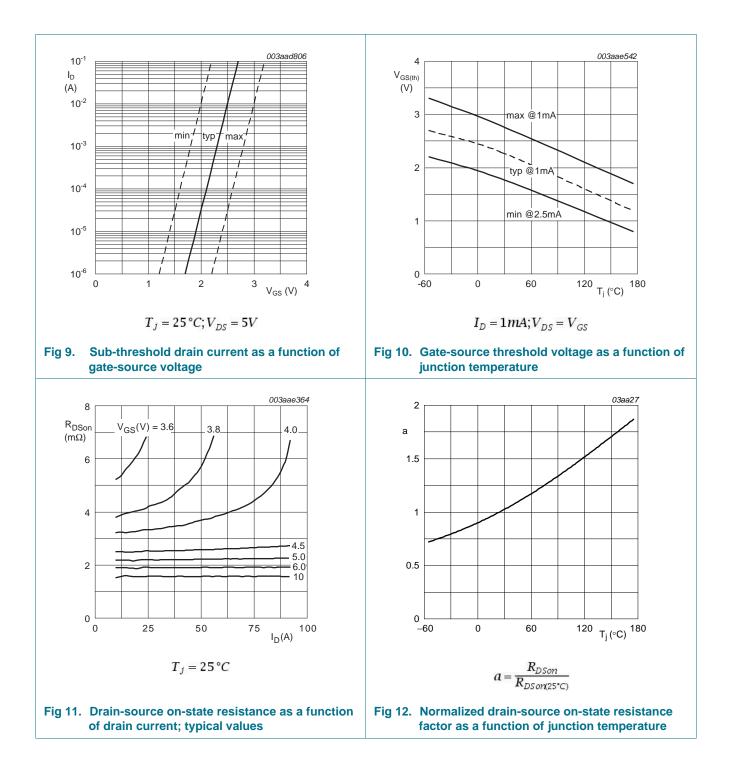
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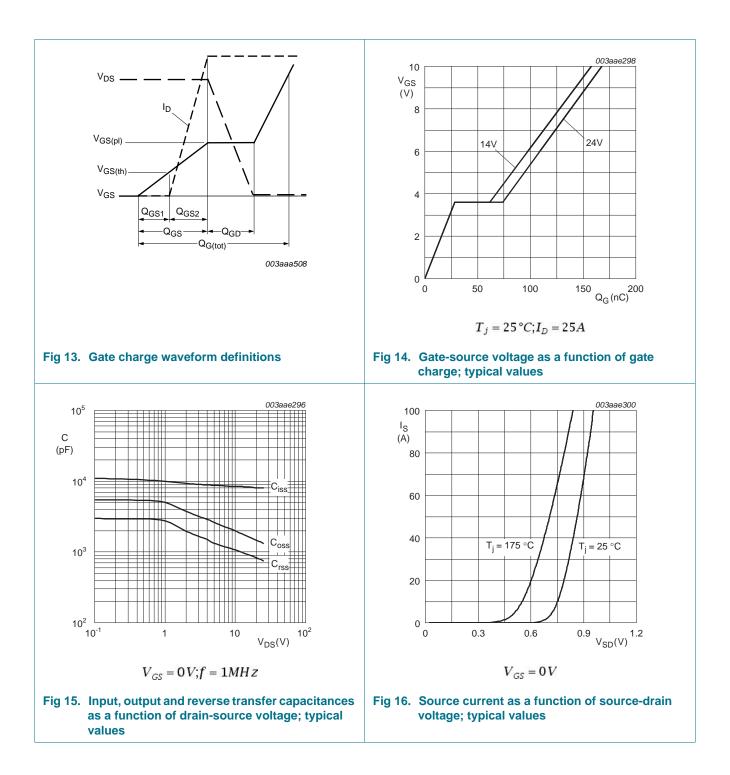


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7. Package outline

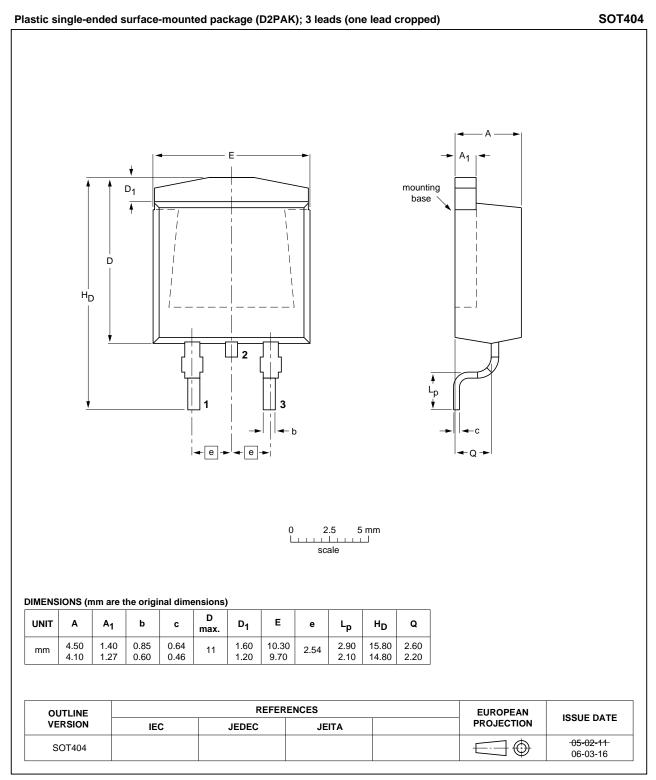


Fig 17. Package outline SOT404 (D2PAK)

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8. Revision history

Table 7.	Revision history	
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Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK661R8-30C v.2.1	20110818	Product data sheet	-	BUK661R8-30C v.2
Modifications:	 Various changes to 	o content.		
BUK661R8-30C v.2	20101228	Product data sheet	-	BUK661R8-30C v.1

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9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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